# Integrated Synchronous Buck Converter

# 6 A

NCP3136 is a fully integrated synchronous buck converter for 3.3 V and 5 V step-down applications. It can provide up to 6.5 A instantaneous current. NCP3136 supports high efficiency, fast transient response and provides power good indicator. The control scheme includes two operation modes: FCCM and automatic CCM/DCM. In automatic CCM/DCM mode, the controller can smoothly switch between CCM and DCM, where converter runs at reduced switching frequency with much higher efficiency. NCP3136 is available in 3 mm x 3 mm QFN16 pin package.

## Features

- High Efficiency in Both CCM and DCM
- Operation Frequency: 1.1 MHz
- Support MLCC Output Capacitor
- Small Footprint, 3 mm x 3 mm, 16-pin QFN Package
- 2.9 V to 5.5 V Wide Conversion Voltage Range
- Output Voltage Range from 0.6 V to 0.84 X  $V_{IN}$
- Automatic Power-Saving Mode
- Voltage Mode Control
- Support Pre-bias Start-up Functionality
- Output Discharge Operation
- Over-Temperature Protection
- Built-in Over-Voltage, Under-Voltage and Over-Current Protection
- Power Good Indicator
- This Device is Pb-Free and is RoHS Compliant

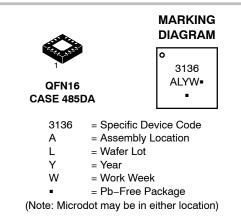
## Applications

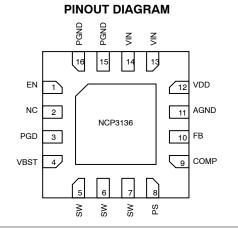
- 5 V Step Down Rail
- 3.3 V Step Down Rail



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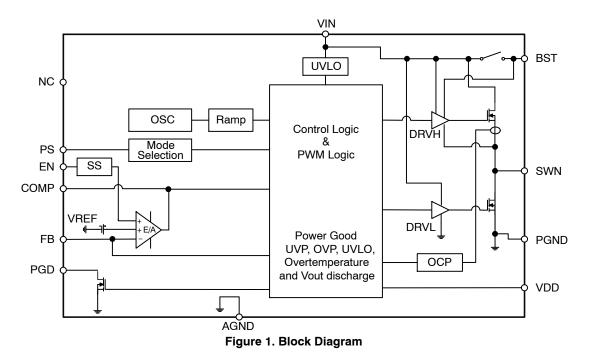




## **ORDERING INFORMATION**

| Device       | Package            | Shipping <sup>†</sup> |  |  |
|--------------|--------------------|-----------------------|--|--|
| NCP3136MNTXG | QFN16<br>(Pb-Free) | 3000 / Tape &<br>Reel |  |  |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.



#### PIN DESCRIPTION

| Pin No. | Symbol | Description   |
|---------|--------|---|
| 1       | EN     | Logic control to enabling the switcher. Internally pulled up to VDD with a 1.35 M $\Omega$ resistor.  |
| 2       | NC     | Not connected.  |
| 3       | PGD    | Open drain power good output.   |
| 4       | BST    | Gate drive voltage for high side FET. Connect capacitor from this pin to SWN.   |
| 5,6,7   | SWN    | Switch node between high-side MOSFET and low-side MOSFET.   |
| 8       | PS     | Mode configuration pin:<br>Connecting to ground: Forced CCM<br>Pulled high or floating (internal pulled high): Forced CCM<br>Connect with 24.3 kΩ to GND: Automatic CCM/DCM<br>Connect with 57.6 kΩ to GND: Automatic CCM/DCM<br>Connect with 105 kΩ to GND: Automatic CCM/DCM<br>Connect with 174 kΩ to GND: Automatic CCM/DCM |
| 9       | COMP   | Output of the error amplifier.  |
| 10      | FB     | Feedback pin. Connect to resistor divider to set up the desired output voltage.   |
| 11      | AGND   | Analog ground   |
| 12      | VDD    | Power supply input for control circuitry.   |
| 13,14   | VIN    | Power input for power conversion and gate driver supply.  |
| 15,16   | PGND   | Power ground  |

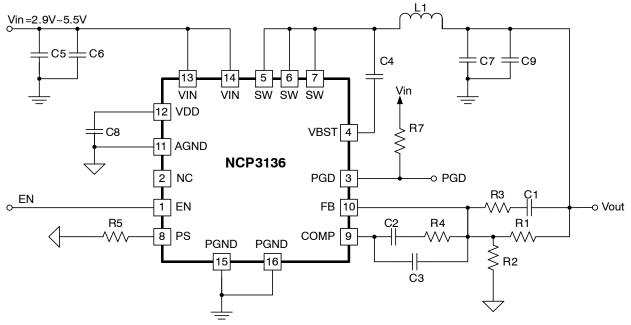


Figure 2. Application Circuit

#### **ABSOLUTE MAXIMUM RATINGS**

|  |         | Condition                    |         | Value     |      |  |
|--|---------|------------------------------|---------|-----------|------|--|
| Parameter  |         |                              |         | Min Max   |      |  |
| Input Voltage Range  |         | VIN, PS                      | -0.3    | 6.5       | V    |  |
|  |         | VBST                         | -0.3    | 17        | 1    |  |
|  | VBST    | (with respect to SW)         | -0.3    | 6.5       | 1    |  |
|  |         | EN, FB                       | -0.3    | VDD + 0.3 |      |  |
| Output Voltage Range   | SW      | DC                           | -1      | 6.5       | V    |  |
|  |         | Pulse < 20 ns, E = 5 $\mu$ J | -3      | 10        | 1    |  |
|  |         | PGD                          |         | 6.5       | 1    |  |
|  |         | COMP                         |         | VDD + 0.3 | 1    |  |
|  |         | PGND                         |         | 0.3       |      |  |
| Operation ambient temperature                                |         | T <sub>A</sub>               | -40 125 |           | °C   |  |
| Storage temperature  |         | T <sub>S</sub>               | -55     | 150       |      |  |
| Junction temperature   |         | TJ                           | -40     | 150       | 1    |  |
| Thermal Characteristics                                      |         | R <sub>θJA</sub>             |         | 45.4      | °C/W |  |
| Electrostatic Discharge                                      | Humar   | Human Body Model (HBM)       |         | 2000      |      |  |
|  | Chargeo | Charged Device Model (CDM)   |         | 2000      | 1    |  |
| Lead temperature 1.6 mm (1/16 inch) from case for 10 seconds |         |                              | 300     |           | °C   |  |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## **RECOMMENDED OPERATION RATINGS**

|  |                           | Value |     |      |      |
|--|---------------------------|-------|-----|------|------|
| Parameter                                  | Condition                 | Min   | Тур | Max  | Unit |
| Input Voltage Range                        | VIN                       | 2.9   |     | 5.5  | V    |
|  | VBST                      | -0.1  |     | 13.5 | 1    |
|  | VBST (with respect to SW) | -0.1  |     | 6.0  | 1    |
|  | EN, PS, FB                | -0.1  |     | VDD  | 1    |
| Output Voltage Range                       | VDD                       | 2.9   |     | 5.5  | V    |
|  | SW                        | -1    |     | 6.5  | 1    |
|  | PGD                       | -0.1  |     | 6.0  | 1    |
|  | СОМР                      | -0.1  |     | VDD  | 1    |
|  | PGND                      | -0.1  |     | 0.1  | 1    |
| Junction temperature range, T <sub>J</sub> |                           | -40   |     | 125  | °C   |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

#### **ELECTRICAL CHARACTERISTICS**

 $(V_{DD} = V_{IN} = 3.3 \text{ V}, T_A = T_J = -40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$ . Typical values are at  $T_A = 25^{\circ}\text{C}$ , PGND = GND unless otherwise noted)

| Parameter   | SYMBOL               | Test Conditions                                      | Min  | Тур  | Max  | Unit  |
|---|----------------------|--|------|------|------|-------|
| POWER SUPPLY                                      |                      |  |      |      | •    |       |
| VIN operation voltage                             | VIN                  | Nominal input voltage range                          | 2.9  |      | 5.5  | V     |
| VIN UVLO threshold                                |                      | Ramp up; EN = 'HI'                                   |      | 2.8  |      | V     |
| VIN UVLO hysteresis                               |                      |  |      | 110  |      | mV    |
| VOLTAGE MONITOR                                   |                      |  |      |      |      |       |
| Power good low voltage                            |                      | Pull-down voltage with 4 mA sink current             |      | 60   | 200  | mV    |
| Power good high leakage current                   |                      |  | -2.0 | 0    | 2.0  | μA    |
| Power good threshold                              |                      | Feedback lower voltage limit                         | 80   | 83   | 86   | %Vre  |
| Power good threshold                              |                      | Feedback higher voltage limit                        | 114  | 117  | 120  | %Vre  |
| Power good high delay                             | t <sub>PGDELAY</sub> |  |      | 400  |      | μs    |
| Output over-voltage protection threshold at FB    |                      |  | 114  | 117  | 120  | %Vref |
| Over-voltage blanking time                        | T <sub>OVPDLY</sub>  | Time from FB higher than 20% of Vref<br>to OVP fault | 1.0  | 1.5  | 2.5  | μs    |
| Output under-voltage protection threshold at FB   |                      |  | 80   | 83   | 86   | %Vre  |
| Under-voltage blanking time                       | T <sub>UVPDLY</sub>  | Time from FB lower than 20% of Vref to UVP fault     |      | 11   |      | μs    |
| SUPPLY CURRENT (T <sub>J</sub> = +25°C)           |                      |  |      | •    | -    |       |
| VIN quiescent current                             | Ivin                 | EN = 'HI', no switching                              |      | 1.5  | 3.5  | mA    |
| VIN shutdown supply current                       | Ivin_sd              | EN = 'LO'  |      |      | 15   | μA    |
| FEEDBACK VOLTAGE & ERROR A                        | <b>IPLIFIER</b>      |  |      |      |      |       |
| Reference voltage at FB                           | VREF                 |  | 594  | 600  | 606  | mV    |
| Unity gain bandwidth (Note 1)                     |                      |  | 14   |      |      | MHz   |
| Open loop gain (Note 1)                           |                      |  | 80   |      |      | dB    |
| FB pin leakage current                            |                      |  |      |      | 100  | nA    |
| Output sourcing and sinking current (Note 1)      |                      | C <sub>comp</sub> = 20 pF                            |      | 5    |      | mA    |
| Slew rate (Note 1)                                |                      |  |      | 5    |      | V/μs  |
| <b>OVER CURRENT PROTECTION &amp; Z</b>            | ERO CROSS            | NG   |      |      | •    |       |
| Over-current limit on high-side FET               |                      |  | 7.6  | 8.2  | 8.8  | A     |
| Hiccup time duration                              | t <sub>hiccup</sub>  | F <sub>sw</sub> = 1.1 MHz                            |      | 14.5 |      | ms    |
| Zero crossing comparator internal offset (Note 1) |                      | PGND-SWN, Automatic CCM/DCM mode                     | -4.5 | -3.0 | -1.5 | mV    |
| LOGIC PINS:I/O VOLTAGE AND CU                     | RRENT                |  |      |      |      |       |
| EN high threshold voltage                         |                      |  | 1.1  | 1.18 | 1.30 | V     |
| EN hysteresis                                     |                      |  |      | 0.18 | 0.24 | V     |
| EN input pull up resistor                         |                      |  |      | 1.2  |      | MΩ    |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Guaranteed by design, not production tested.

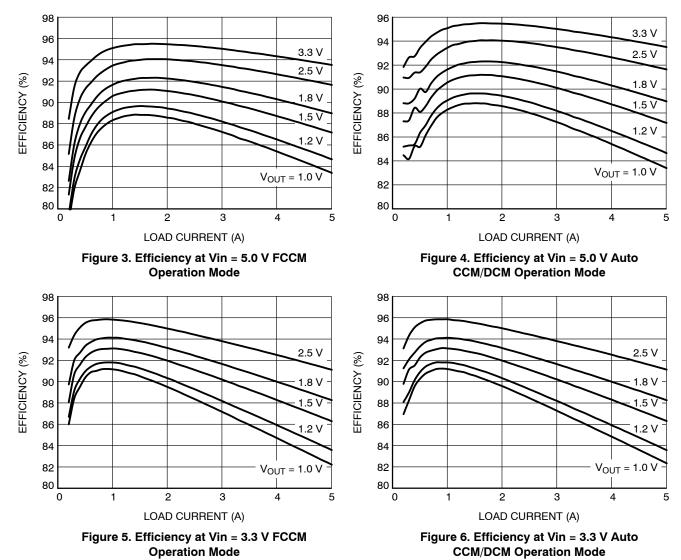
## **ELECTRICAL CHARACTERISTICS**

 $(V_{DD} = V_{IN} = 3.3 \text{ V}, \text{ } T_A = T_J = -40^{\circ}\text{C} \text{ to } +125^{\circ}\text{C}. \text{ Typical values are at } T_A = 25^{\circ}\text{C}, \text{ PGND} = \text{GND} \text{ unless otherwise noted})$ 

| Parameter  | SYMBOL            | Test Conditions  | Min    | Тур                | Max  | Unit |
|--|-------------------|--|--------|--------------------|------|------|
|  |                   |  | IVIIII | ιγρ                | WIGA | onit |
| LOGIC PINS:I/O VOLTAGE AND CU                              |                   |  | -      | 1                  | 1    | 1    |
| PS mode threshold voltage                                  | PS <sub>THS</sub> | Level 1 to Level 2   |        | 0.05               |      | V    |
|  |                   | Level 2 to Level 3   |        | 1.3                |      |      |
| PS source current  | I <sub>PS</sub>   | 7 $\mu$ A pull-up current when enabled   |        | 7                  |      | μA   |
| INTERNAL BST DIODE   |                   |  |        |                    |      |      |
| Reverse-bias leakage current                               |                   | $V_{BST} = 6.6 \text{ V}, \text{ V}_{IN} = 3.3 \text{ V}, \text{ Ta} = 25^{\circ}\text{C}$ |        |                    | 1    | μA   |
| SOFT STOP  |                   |  | •      |                    |      |      |
| Output discharge on-resistance                             |                   | $EN = 0, V_{IN} = 3.3 V, V_{OUT} = 0.5 V$  |        | 36                 |      | Ω    |
| TIMERS: SOFT-START   |                   |  |        |                    | •    |      |
| Soft-Start ramp-up time                                    | Tss               | Rising from V <sub>SS</sub> = 0 V to V <sub>SS</sub> = 0.6 V                               |        | 1.5                |      | ms   |
| Delay after EN asserting                                   |                   | EN = 'HI'  |        | 0.5                |      | ms   |
| Switching Frequency Control                                |                   | FCCM mode<br>Frequency setting = 1.1 MHz   | 0.99   | 1.10               | 1.21 | MHz  |
| PWM  | •                 |  |        |                    |      |      |
| Minimum OFF time   |                   | FCCM mode or<br>Automatic CCM/DCM mode   |        | 100                | 140  | ns   |
| PWM ramp amplitude (Note 1)                                |                   | 2.9 V< V <sub>IN</sub> < 6.0 V   |        | V <sub>IN</sub> /4 |      | V    |
| Maximum duty cycle, FCCM mode<br>or Automatic CCM/DCM mode |                   | F <sub>SW</sub> = 1.1 MHz  | 84%    | 89%                |      |      |
| THERMAL SHUTDOWN   | •                 |  |        |                    |      |      |
| Thermal shutdown threshold (Note 1)                        |                   |  | 130    | 140                | 150  | °C   |
| Thermal shutdown hysteresis<br>(Note 1)                    |                   |  |        | 40                 |      | °C   |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 1. Guaranteed by design, not production tested.

# **TYPICAL CHARACTERISTICS**



## **DETAILED DESCRIPTION**

#### Overview

NCP3136 is a low input voltage high performance synchronous buck converter with two integrated N–MOSFETs. NCP3136's output voltage range is from 0.6 V to 0.84 x Vin and it has wide input voltage range from 2.9 V to 5.5 V. The features of NCP3136 include supporting pre–bias start–up to protect sensitive loads, cycle–by–cycle over–current limiting and short circuit protection, power good monitor, over voltage and under voltage protection, built in output discharge and thermal shutdown.

NCP3136 provides two operation modes to fit various application requirements. The automatic CCM/DCM mode operation provides reduced power loss and increases the efficiency at light load. The adaptive power control architecture enables smooth transition between light load and heavy load while maintaining fast response to load transients.

#### **Operation Mode**

In forced continuous conduction mode (FCCM), the high-side FET is ON during the on-time and the low-side FET is ON during the off-time. The switching is synchronized to an internal clock thus the switching frequency is fixed.

In Automatic CCM/DCM mode, the high-side FET is ON during the on-time and low-side FET is ON during the off-time until the inductor current reaches zero. An internal zero-crossing comparator detects the zero crossing of the inductor current from positive to negative. When the inductor current reaches zero, the comparator sends a signal to the logic circuitry and turns off the low-side FET.

When the load is increased, the inductor current is always positive and the zero-crossing comparator does not send any zero-crossing signal. The converter enters into continuous conduction mode (CCM) when no zero-crossing is detected for two consecutive PWM pulses. In CCM mode, the switching synchronizes to the internal clock and the switching frequency is fixed.

## **VDD Voltage**

The VDD voltage is supplied from VIN via an intrenal resistor. Meanwhile, it is also ok to short the VDD pin and VIN pins externally.

## Reference Voltage

The NCP3136 incorporates 600 mV reference voltage with 1.0% tolerance.

#### Internal Soft-Start

To limit the start–up inrush current, an internal soft start circuit is used to ramp up the reference voltage from 0 V to its final value linearly. The internal soft start time is 2.0 ms typically.

#### Soft Stop

Soft–Stop or discharge mode is always on during faults or disable. In this mode, disable (EN) causes the output to be discharged through an internal 40  $\Omega$  transistor inside of SW terminal. The time constant of soft–stop is a function of output capacitance and the resistance of the discharge transistor.

#### Automatic Power Saving Mode

In Automatic CCM/DCM mode when the load current decreases, the converter will enter power saving mode operation. During power saving mode, the low-side MOSFET will turn off when the inductor current reaches zero. So the converter skips switching and operates with reduced frequency, which minimizes the quiescent current and maintains high efficiency.

#### **Forced Continuous Conduction Mode**

When PS pin is floating or pulled high, NCP3136 is operating in forced continuous conduction mode in both light load and heavy load conditions. In this mode, the switching frequency remains constant over the entire load range, making it suitable for applications that need tight regulation of switching frequency at a cost of lower efficiency at light load.

## PROTECTIONS

#### Under Voltage Lockout (UVLO)

There is under-voltage lock out protection (UVLO) for VIN in NCP3136, which has a typical trip threshold voltage 2.8 V and trip hysteresis 130 mV for VIN. If UVLO is triggered, the device resets and waits for the voltage to rise up over the threshold voltage and restart the part. Please note this protection function DOES NOT trigger the fault counter to latch off the part.

#### **Over Voltage Protection (OVP)**

When feedback voltage is above 17% (typical) of nominal voltage for over 1.7  $\mu$ s blanking time, an OV fault is set. In this case, the converter de-asserts the PGD signal and performs the over-voltage protection function. The top gate drive is turned off and the bottom gate drive is turned on to discharge the output. The bottom gate drive will be turned off until VFB drops below the UVP threshold. The device enters a high-impedance state. This protection is latched.

#### **Under Voltage Protection (UVP)**

Output under-voltage protection works in conjunction with the current protection described in the Over-current Protection sections. An UVP circuit monitors the feedback voltage to detect under-voltage event. The under-voltage limit is 17% (typical) below of nominal voltage at FB pin. If the feedback voltage is below this threshold over 11  $\mu$ s, an UV fault is set and both the high-side and the low-side FETs turn off. After a hiccup delay, the part tries to restart. This protection behavior is hiccup.

#### **Power Good Monitor (PGD)**

NCP3136 provides window comparator to monitor the output voltage at FB pin. When the output voltage is within  $\pm 17\%$  of regulation voltage, the power good pin outputs a high signal. Otherwise, PGD stays low. The PGD pin is open drain 5 mA pull down output. During startup, PGD stays low until the feedback voltage is within the specified range for about 0.4 ms. If feedback voltage falls outside the tolerance band, the PG pin goes low after 10 µs delay.

The PGD pin de-asserts as soon as the EN pin is pulled low or an under-voltage event on VDD is detected.

#### **Over Current Protection (OCP)**

NCP3136 provides high-side MOSFET current limiting. When the current through the high-side FET exceeds 7.5 A, the high-side FET turns off and the low-side FET turns on until next PWM cycle. An over-current counter is triggered and starts to increment each occurrence of an over-current event. Both the high-side and the low-side FETs turn off when the OC counter reaches four. The OC counter resets if the detected current is less than 7.5 A after an OC event.

#### **Pre-Bias Startup**

In some applications the controller will be required to start switching when its output capacitors are charged anywhere from slightly above 0 V to just below the regulation voltage. This situation occurs for a number of reasons: the converter's output capacitors may have residual charge on them or the converter's output may be held up by a low current standby power supply. NCP3136 supports pre-bias start up by holding low-side FETs off until soft start ramp reaches the FB pin voltage.

#### Thermal Shutdown

The NCP3136 protects itself from over heating with an internal thermal monitoring circuit. When the die temperature goes beyond a threshold value 135°C, both the high–side and the low–side FETs turn off until the temperature falls 40°C below of the threshold value. Then the converter restarts.

#### **Application Note**

For higher output voltage application cases (Vout = 3.3 V), choose the inductor value not to be lower than 1  $\mu$ H to avoid over-current protection being triggered by inductor current ripple; For Vin = 5 V and Vout = 3.3 V case, add a voltage divider between Vin and EN to ensure that the part can start up without triggering UVP. Use Figure 7 as design reference for schematics. For other lower output voltage cases, it is not necessary to add this divider.

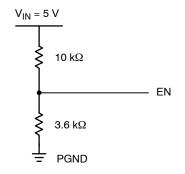


Figure 7. Voltage divider between VIN and EN for start-up in VIN = 5 V and VOUT = 3.3 V case

#### Layout Guidelines

When laying out a power PCB for the NCP3136 there are several key points to consider.

Use four vias to connect the thermal pad to power ground. Separate the power ground and analog ground planes; connect them together at a single point.

Increase the thickness of PCB copper, it can help to lower the die temperature and improve the overall efficiency but meanwhile increase the cost of the board fabrication.

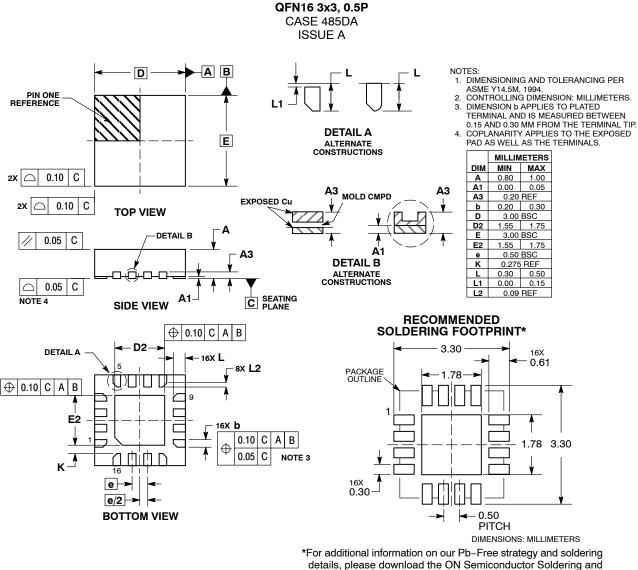
Use wide traces for the nodes conducting high current such as VIN, VOUT, PGND and SW.

Place feedback and compensation network components close to the IC.

Keep FB, COMP away from noisy signals such as SW, BST.

Place VIN and VDD decoupling capacitors as close to the IC as possible.

#### PACKAGE DIMENSIONS



details, please download the ON Semiconductor Soldering a Mounting Techniques Reference Manual, SOLDERRM/D.

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